



GP
ELECTRONICS

B1040WS
40V-1A Schottky Barrier Diode

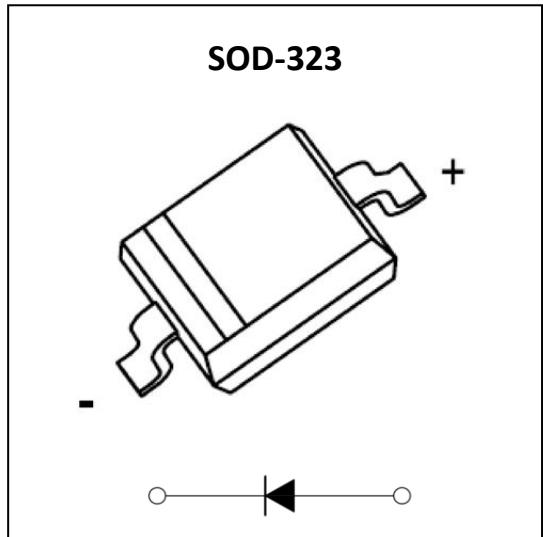
B1040WS Schottky Barrier Diode

Feature

- Low Forward Voltage Drop
- Low Reverse current
- Very Small SMD Package

Application

- Low Voltage Rectification
- High Efficiency DC/DC Conversion
- Switch Mode Power Supply
- Inverse Polarity Protection
- Low Power Consumption Applications



MARKING:



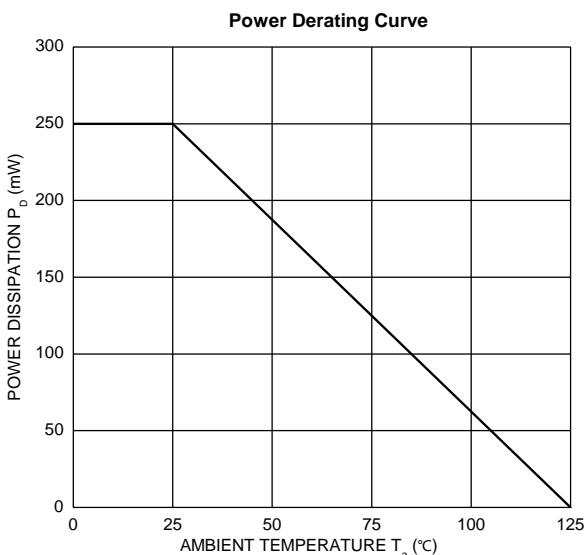
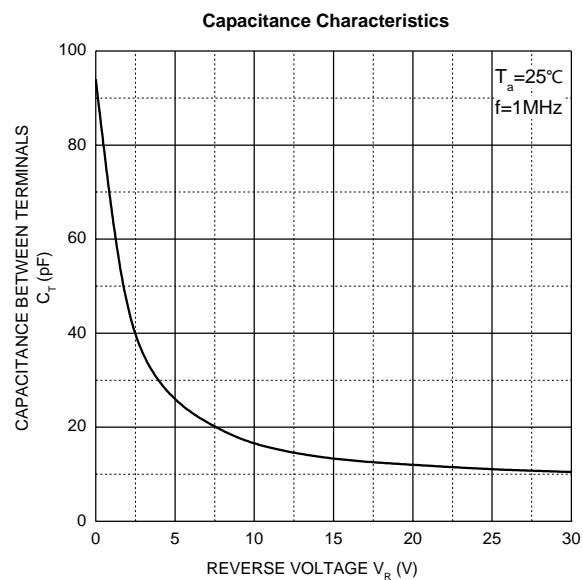
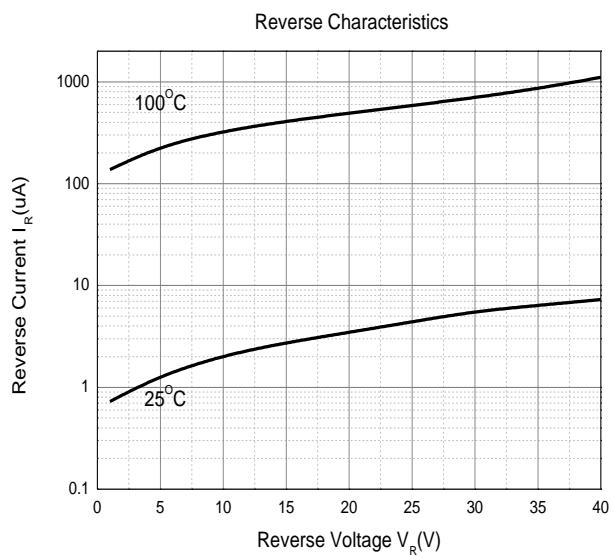
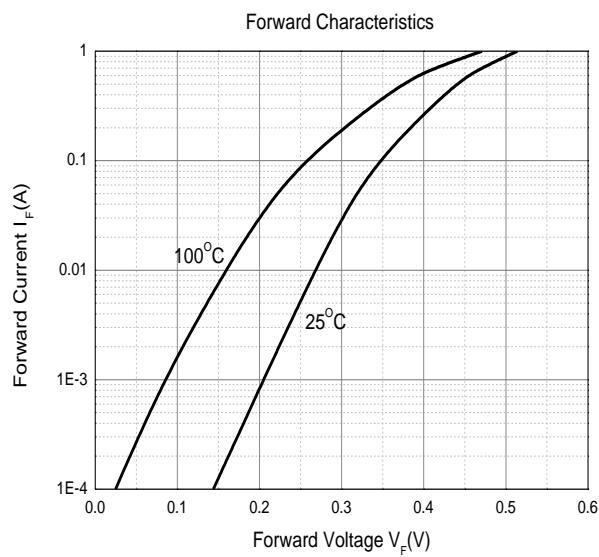
ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

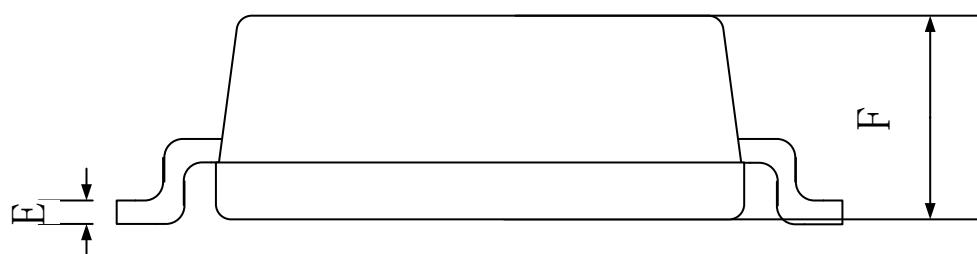
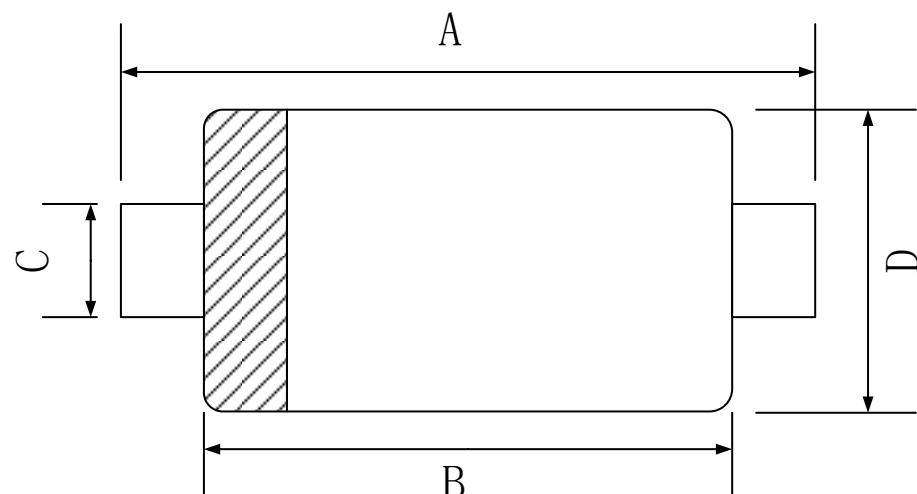
Parameter	Symbol	Value	Unit
DC reverse voltage	V_R	40	V
Mean rectifying current	I_O	1	A
Non-repetitive Peak Forward Surge Current @ $t=8.3\text{ms}$	I_{FSM}	9	A
Power Dissipation	P_D	0.25	W
Thermal Resistance from Junction to Ambient	R_{JA}	400	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	125	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 ~ +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Reverse voltage	V_{BR}	$I_R = 250\mu\text{A}$	40			V
Reverse current	I_R	$V_R = 20\text{V}$		2	20	μA
		$V_R = 40\text{V}$		5	50	μA
Forward voltage	V_F	$I_F = 0.5\text{A}$		0.45	0.50	V
		$I_F = 0.7\text{A}$		0.48	0.54	V
		$I_F = 1\text{A}$		0.5	0.62	V
Diode capacitance	C_D	$VR=10\text{V}, f=1\text{MHz}$		18		pF

Typical Characteristics



SOD-323 Package Outline Dimensions


Symbol	Dimensions In Millimeters		
	Min.	Typ.	Max.
A	2.30	2.50	2.70
B	1.60	1.70	1.90
C	0.25	0.325	0.40
D	1.15	1.25	1.35
E	0.089	0.095	0.101
F	0.80	0.90	1.00